



# 2x2 LVDS CROSSPOINT SWITCH

#### **FEATURES**

- High Speed (>1000 Mbps) Upgrade for DS90CP22 2x2 LVDS Crosspoint Switch
- LVPECL Crosspoint Switch Available in SN65LVCP23
- Low-Jitter Fully Differential Data Path
- 50 ps (Typ), of Peak-to-Peak Jitter With PRBS = 2<sup>23</sup>–1 Pattern
- Less Than 200 mW (Typ), 300 mW (Max) Total Power Dissipation
- Output (Channel-to-Channel) Skew Is 10 ps (Typ), 50 ps (Max)
- Configurable as 2:1 Mux, 1:2 Demux, Repeater or 1:2 Signal Splitter
- Inputs Accept LVDS, LVPECL, and CML Signals
- Fast Switch Time of 1.7 ns (Typ)
- Fast Propagation Delay of 0.65 ns (Typ)
- 16 Lead SOIC and TSSOP Packages
- Inter-Operates With TIA/EIA-644-A LVDS Standard
- Operating Temperature: –40°C to 85°C

#### **APPLICATIONS**

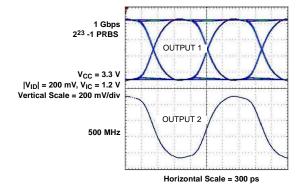
- Base Stations
- Add/Drop Muxes
- Protection Switching for Serial Backplanes
- Network Switches/Routers
- Optical Networking Line Cards/Switches
- Clock Distribution

#### DESCRIPTION

The SN65LVCP22 is a 2×2 crosspoint switch providing greater than 1000 Mbps operation for each dual channels incorporate common-mode (0 V to 4 V) receivers, allowing for the receipt of LVDS, LVPECL, and CML signals. The dual outputs are LVDS drivers to provide low-power. low-EMI, high-speed operation. The SN65LVCP22 provides a single device supporting 2:2 buffering (repeating), 1:2 splitting, 2:1 multiplexing, 2×2 switching, and LVPECL/CML to LVDS level switching, translation on each channel. The flexible operation of the SN65LVCP22 provides a single device to support the redundant serial bus transmission needs (working and protection switching cards) of fault-tolerant switch systems found in optical networking, wireless infrastructure, and data commu- nications systems. TI offers additional gigibit repeater/ translator and crosspoint products in the SN65LVDS100 and SN65LVDS122.

The SN65LVCP22 uses a fully differential data path to ensure low-noise generation, fast switching times, low pulse width distortion, and low jitter. Output channel-to- channel skew is less than 10 ps (typ) and 50 ps (max) to ensure accurate alignment of outputs in all applications. Both SOIC and TSSOP package options are available to allow easy upgrade for existing solutions, and board area savings where space is critical.

#### **OUTPUTS OPERATING SIMULTANEOUSLY**





Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.





These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

#### **ORDERING INFORMATION**

PACKAGE DESIGNATOR	PART NUMBER <sup>(1)</sup>	SYMBOLIZATION
SOIC	SN65LVCP22D	LVCP22
TSSOP	SN65LVCP22PW	LVCP22

(1) Add the suffix R for taped and reeled carrier

#### **PACKAGE DISSIPATION RATINGS**

PACKAGE	PACKAGE CIRCUIT BOARD MODEL		DERATING FACTOR <sup>(1)</sup> ABOVE T <sub>A</sub> = 25°C	T <sub>A</sub> = 85°C POWER RATING
SOIC (D)	High-K <sup>(2)</sup>	1361 mW	13.9 mW/°C	544 mW
TSSOP (PW)	High-K <sup>(2)</sup>	1074 mW	10.7 mW/°C	430 mW

- 1) This is the inverse of the junction-to-ambient thermal resistance when board-mounted and with no air flow.
- (2) In accordance with the High-K thermal metric definitions of EIA/JESD51-7.

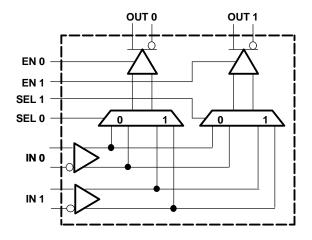
#### THERMAL CHARACTERISTICS

	PARAMETER		TEST CONDITIONS	VALUE	UNITS
$\theta_{JB}$	Junction-to-board thermal resistance	D		11.2	°C/W
	Junction-to-board thermal resistance	PW		18.4	C/VV
0	Junction-to-case thermal resistance	D		23.7	°C/W
$\theta_{JC}$		PW		16.0	C/VV
D	Davisa power dissipation	Typical	V <sub>CC</sub> = 3.3 V, T <sub>A</sub> = 25°C, 1 Gbps	198	mW
$P_{D}$	Device power dissipation	Maximum	V <sub>CC</sub> = 3.6 V, T <sub>A</sub> = 85°C, 1 Gbps	313	IIIVV

## **FUNCTION TABLE**

SEL0	SEL1	OTT0	OUT1	FUNCTION
0	0	IN0	IN0	1:2 Splitter
0	1	IN0	IN1	Repeater
1	0	IN1	IN0	Switch
1	1	IN1	IN1	1:2 Splitter

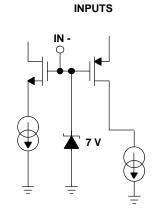
#### **FUNCTIONAL BLOCK DIAGRAM**

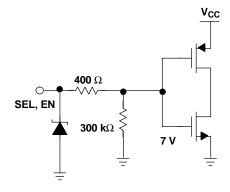




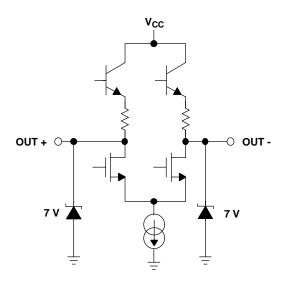
# **EQUIVALENT INPUT AND OUTPUT SCHEMATIC DIAGRAMS**

# 7V - - - -





#### **OUTPUTS**



#### **ABSOLUTE MAXIMUM RATINGS**

over operating free-air temperature range unless otherwise noted (1)

Supply voltage(2) range, \	Supply voltage (2) range, V <sub>CC</sub>						
CMOS/TTL input voltage	(ENO, EN1, SEL0, SEL1)		–0.5 V to 4 V				
LVDS receiver input volta	ge (IN+, IN-)		–0.7 V to 4.3 V				
LVDS driver output voltag	LVDS driver output voltage (OUT+, OUT-)						
LVDS output short circuit	current		Continuous				
Storage temperature rang	je		−65°C to 125°C				
Lead temperature 1,6 mm	n (1/16 inch) from case for 10	seconds	235°C				
Continuous power dissipa	ition		See Dissipation Rating Table				
Human body model <sup>(3)</sup>		All pins	±5 kV				
Electrostatic discharge	Charged-device mode (4)	All pins	±500 V				

<sup>(1)</sup> Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

<sup>2)</sup> All voltage values, except differential I/O bus voltages, are with respect to network ground terminals.

<sup>(3)</sup> Tested in accordance with JEDEC Standard 22, Test Method A114-A.

Tested in accordance with JEDEC Standard 22, Test Method C101.



# RECOMMENDED OPERATING CONDITIONS

	MIN	NOM	MAX	UNIT
Supply voltage, V <sub>CC</sub>	3	3.3	3.6	V
Receiver input voltage	0		4	V
Junction temperature			125	°C
Operating free-air temperature, T <sub>A</sub> <sup>(1)</sup>	-40		85	°C
Magnitude of differential input voltage  V <sub>ID</sub>	0.1		3	V

<sup>(1)</sup> Maximum free-air temperature operation is allowed as long as the device maximum junction temperature is not exceeded.

# INPUT ELECTRICAL CHARACTERISTICS

over recommended operatingconditions unless otherwise noted

	PARAMETER	TEST CONDITIONS	MIN	TYP <sup>(1)</sup>	MAX	UNIT
CMOS/T	TL DC SPECIFICATIONS (EN0, EN1, SEL0, SEL1)		'			
V <sub>IH</sub>	High-level input voltage		2		$V_{CC}$	V
V <sub>IL</sub>	Low-level input voltage		GND		0.8	V
I <sub>IH</sub>	High-level input current	V <sub>IN</sub> = 3.6 V or 2.0 V, V <sub>CC</sub> = 3.6 V		±3	±20	μΑ
I <sub>IL</sub>	Low-level input current	V <sub>IN</sub> = 0.0 V or 0.8 V, V <sub>CC</sub> = 3.6 V		±1	±10	μΑ
$V_{CL}$	Input clamp voltage	I <sub>CL</sub> = -18 mA		-0.8	-1.5	V
LVDS O	UTPUT SPECIFICATIONS (OUT0, OUT1)		1			
		$R_L = 75 \Omega$ , See Figure 2	270	365	475	
V <sub>OD</sub>	Differential output voltage	$R_L$ = 75 $\Omega$ , $V_{CC}$ = 3.3 V, $T_A$ = 25°C, See Figure 2	285	365	440	mV
$\Delta  V_{OD} $	Change in differential output voltage magnitude between logic states	V <sub>ID</sub> = ±100 mV, See Figure 2	-25		25	mV
Vos	Steady-state offset voltage	See Figure 3	1	1.2	1.45	V
ΔV <sub>OS</sub>	Change in steady-state offset voltage between logic states	See Figure 3	-25		25	mV
V <sub>OC(PP)</sub>	Peak-to-peak common-mode output voltage	See Figure 3		50	150	mV
I <sub>OZ</sub>	High-impedance output current	V <sub>OUT</sub> = GND or V <sub>CC</sub>			±10	μΑ
I <sub>OFF</sub>	Power-off leakage current	V <sub>CC</sub> = 0 V, 1.5 V; V <sub>OUT</sub> = 3.6 V or GND			±10	μΑ
Ios	Output short-circuit current	V <sub>OUT+</sub> or V <sub>OUT-</sub> = 0 V			-24	mA
I <sub>OSB</sub>	Both outputs short-circuit current	V <sub>OUT+</sub> and V <sub>OUT-</sub> = 0 V	-12		12	mA
Co	Differential output capacitance	$V_I = 0.4 \sin(4E6\pi t) + 0.5 V$		3		pF
LVDS R	ECEIVER DC SPECIFICATIONS (IN0, IN1)					
$V_{TH}$	Positive-going differential input voltage threshold	See Figure 1 and Table 1			100	mV
V <sub>TL</sub>	Negative-going differential input voltage threshold	See Figure 1 and Table 1	-100			mV
V <sub>ID(HYS)</sub>	Differential input voltage hysteresis			25		mV
V <sub>CMR</sub>	Common-mode voltage range	$V_{ID} = 100 \text{ mV}, V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	0.05		3.95	V
	Input ourrent	$V_{IN} = 4 \text{ V}, V_{CC} = 3.6 \text{ V or } 0.0$		±1	±10	
I <sub>IN</sub>	Input current	$V_{IN} = 0 \text{ V}, V_{CC} = 3.6 \text{V or } 0.0$		±1	±10	μA
C <sub>IN</sub>	Differential input capacitance	$V_I = 0.4 \sin (4E6\pi t) + 0.5 V$		3		pF
SUPPLY	CURRENT					
I <sub>CCD</sub>	Total supply current	$R_L = 75 \Omega$ , $C_L = 5 pF$ , 500 MHz (1000 Mbps), EN0=EN1=High		60	87	mA
I <sub>CCZ</sub>	3-state supply current	EN0 = EN1 = Low		25	35	mA

<sup>(1)</sup> All typical values are at 25°C and with a 3.3-V supply.



# **SWITCHING CHARACTERISTICS**

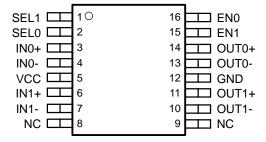
over recommended operating conditions unless otherwise noted

	parameter	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t <sub>SET</sub>	Input to SEL setup time	See Figure 6	1	0.5		ns
t <sub>HOLD</sub>	Input to SEL hold time	See Figure 6	1.1	0.5		ns
t <sub>SWITCH</sub>	SEL to switched output	See Figure 6		1.7	2.5	ns
t <sub>PHZ</sub>	Disable time, high-level-to-high-impedance	See Figure 5		2	4	ns
t <sub>PLZ</sub>	Disable time, low-level-to-high-impedance	See Figure 5		2	4	ns
t <sub>PZH</sub>	Enable time, high-impedance -to-high-level output	See Figure 5		2	4	ns
t <sub>PZL</sub>	Enable time, high-impedance-to-low-level output	See Figure 5		2	4	ns
t <sub>LHT</sub>	Differential output signal rise time (20%-80%) <sup>(1)</sup>	C <sub>L</sub> = 5 pF, See Figure 4	150	280	450	ps
t <sub>HLT</sub>	Differential output signal fall time (20%-80%) <sup>(1)</sup>	C <sub>L</sub> = 5 pF, See Figure 4	150	280	450	ps
	Added pools to pools iitter	$V_{ID}$ = 200 mV, 50% duty cycle, $V_{CM}$ = 1.2 V, 500 MHz, $C_L$ = 5 pF		20	40	ps
t <sub>JIT</sub>	Added peak-to-peak jitter	$V_{ID}$ = 200 mV, PRBS = 2 <sup>23</sup> -1 data pattern, $V_{CM}$ = 1.2 V at 1000 Mbps, $C_L$ = 5 pF		50	105	ps
t <sub>Jrms</sub>	Added random jitter (rms)	$V_{ID}$ = 200 mV, 50% duty cycle, $V_{CM}$ = 1.2 V at 500 MHz, $C_L$ = 5 pF		1.1	1.8	ps <sub>RMS</sub>
t <sub>PLHD</sub>	Propagation delay time, low-to-high-level output <sup>(1)</sup>		400	650	1000	ps
t <sub>PHLD</sub>	Propagation delay time, high-to-low-level output <sup>(1)</sup>		400	650	1000	ps
t <sub>skew</sub>	Pulse skew ( t <sub>PLHD</sub> - t <sub>PHLD</sub>  ) <sup>(2)</sup>	C <sub>L</sub> = 5 pF, See Figure 4		20	100	ps
t <sub>CCS</sub>	Output channel-to-channel skew, splitter mode	C <sub>L</sub> = 5 pF, See Figure 4		10	50	ps
f <sub>MAX</sub>	Maximum operating frequency <sup>(3)</sup>		1			GHz

- Input:  $V_{IC}$  = 1.2 V,  $V_{ID}$  = 200 mV, 50% duty cycle, 1 MHz,  $t_r/t_f$  = 500 ps  $t_{skew}$  is the magnitude of the time difference between the  $t_{PLHD}$  and  $t_{PHLD}$  of any output of a single device. Signal generator conditions: 50% duty cycle,  $t_r$  or  $t_f \le$  100 ps (10% to 90%), transmitter output criteria: duty cycle = 45% to 55%  $V_{OD} \ge$ 300 mV.

#### **PIN ASSIGNMENTS**

### D or PW PACKAGE (TOP VIEW)



NC - No internal connection



#### PARAMETER MEASUREMENT INFORMATION

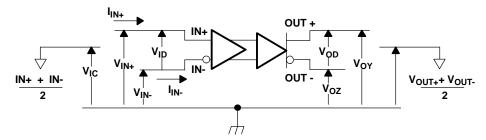


Figure 1. Voltage and Current Definitions

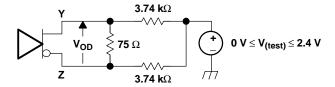
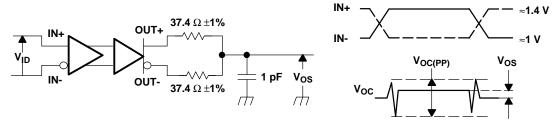


Figure 2. Differential Output Voltage (VoD) Test Circuit

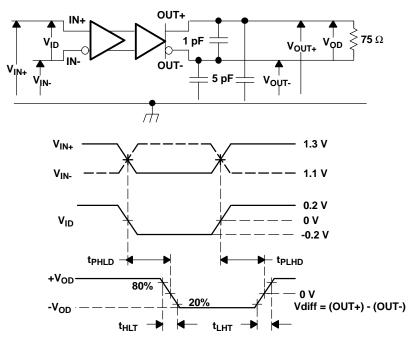


NOTE: All input pulses are supplied by a generator having the following characteristics:  $t_r$  or  $t_f \le 1$  ns, pulse-repetition rate (PRR) = 0.5 Mpps, pulse width = 500 ±10 ns;  $R_L = 100 \ \Omega$ ;  $C_L$  includes instrumentation and fixture capacitance within 0,06 mm of the D.U.T.; the measurement of  $V_{OC(PP)}$  is made on test equipment with a -3 dB bandwidth of at least

Figure 3. Test Circuit and Definitions for the Driver Common-Mode Output Voltage

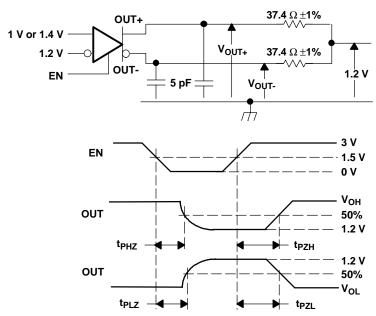


# PARAMETER MEASUREMENT INFORMATION (continued)



NOTE: All input pulses are supplied by a generator having the following characteristics:  $t_r$  or  $t_f \le .25$  ns, pulse-repetition rate (PRR) = 0.5 Mpps, pulse width = 500  $\pm$  10 ns.  $C_L$  includes instrumentation and fixture capacitance within 0,06 mm of the D.U.T.

Figure 4. Timing Test Circuit and Waveforms



NOTE: All input pulses are supplied by a generator having the following characteristics:  $t_r$  or  $t_f \le 1$  ns, pulse-repetition rate (PRR) = 0.5 Mpps, pulse width = 500  $\pm$  10 ns.  $C_L$  includes instrumentation and fixture capacitance within 0,06 mm of the D.U.T.

Figure 5. Enable and Disable Time Circuit and Definitions

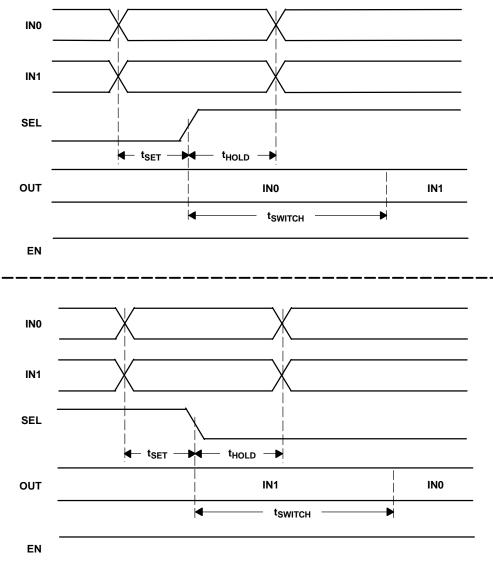


**Table 1. Receiver Input Voltage Threshold Test** 

APPLIED VOLTAGES		RESULTING DIFFERENTIAL INPUT VOLTAGE	RESULTING COMMON- MODE INPUT VOLTAGE	OUTPUT <sup>(1)</sup>
VIA	V <sub>IB</sub>	V <sub>ID</sub>	V <sub>IC</sub>	
1.25 V	1.15 V	100 mV	1.2 V	Н
1.15 V	1.25 V	-100 mV	1.2 V	L
4.0 V	3.9 V	100 mV	3.95 V	Н
3.9 V	4. 0 V	4. 0 V -100 mV 3.95 V		L
0.1 V	0.0 V	100 mV	0.05 V	Н
0.0 V	0.1 V	–100 mV	0.05 V	L
1.7 V	0.7 V	1000 mV	1.2 V	Н
0.7 V	1.7 V	1.7 V -1000 mV 1.2 V		L
4.0 V	3.0 V	1000 mV 3.5 V		Н
3.0 V	4.0 V	–1000 mV	3.5 V	L
1.0 V	0.0 V	1000 mV	0.5 V	Н
0.0 V	1.0 V	–1000 mV	0.5 V	L

<sup>(1)</sup> H = high level, L = low level



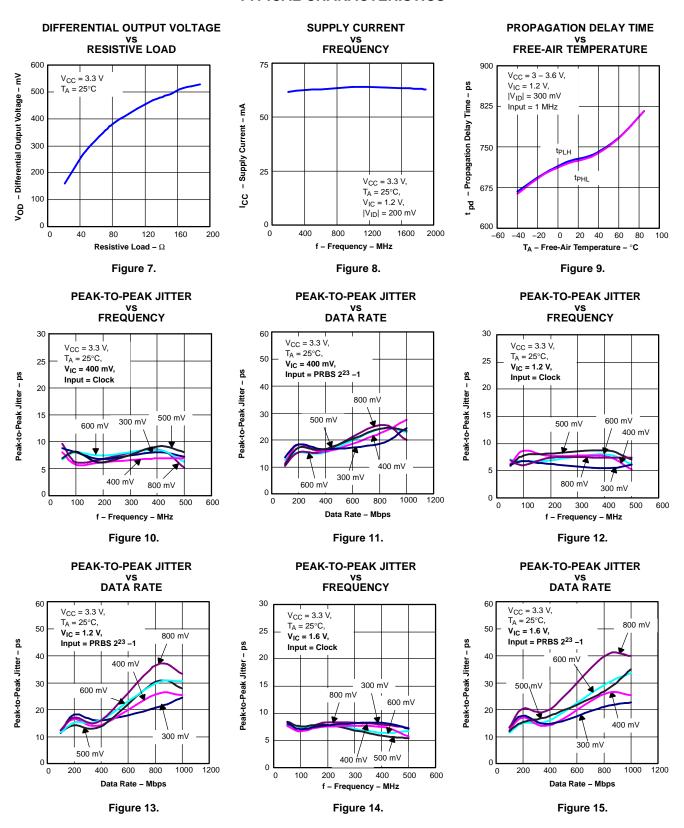


NOTE:  $t_{\text{SET}}$  and  $t_{\text{HOLD}}$  times specify that data must be in a stable state before and after mux control switches.

Figure 6. Input to Select for Both Rising and Falling Edge Setup and Hold Times



#### TYPICAL CHARACTERISTICS





# **TYPICAL CHARACTERISTICS (continued)**

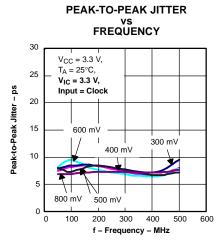
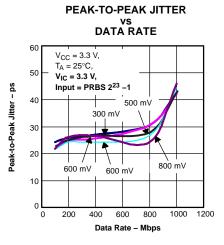


Figure 16.



6. Figure 17.

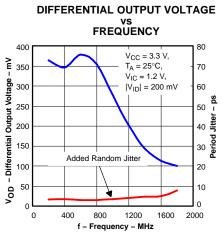


Figure 18.



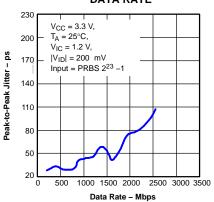


Figure 19.



# **APPLICATION INFORMATION**

# TYPICAL APPLICATION CIRCUITS (ECL, PECL, LVDS, etc.)

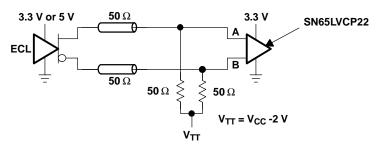


Figure 20. Low-Voltage Positive Emitter-Coupled Logic (LVPECL)

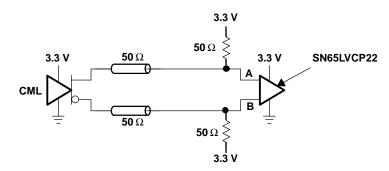


Figure 21. Current-Mode Logic (CML)

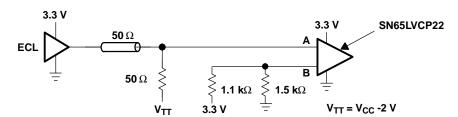


Figure 22. Single-Ended (LVPECL)

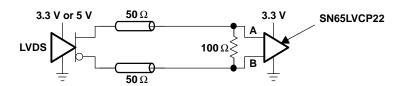


Figure 23. Low-Voltage Differential Signaling (LVDS)



# **APPLICATION INFORMATION (continued)**

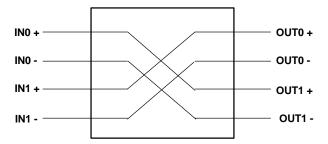


Figure 24. 2 x 2 Crosspoint

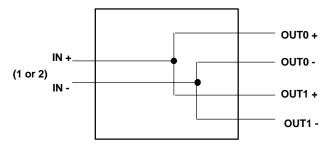


Figure 25. 1:2 Spitter

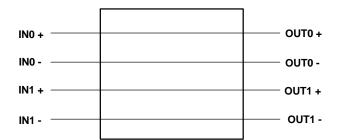


Figure 26. Dual Repeater

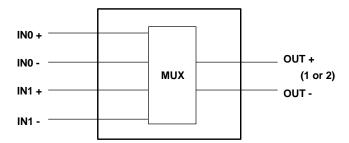


Figure 27. 2:1 MUX

# PACKAGE OPTION ADDENDUM



10-Dec-2020

#### PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
SN65LVCP22D	ACTIVE	SOIC	D	16	40	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	LVCP22	Samples
SN65LVCP22DG4	ACTIVE	SOIC	D	16	40	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	LVCP22	Samples
SN65LVCP22DR	ACTIVE	SOIC	D	16	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	LVCP22	Samples
SN65LVCP22PW	ACTIVE	TSSOP	PW	16	90	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	LVCP22	Samples
SN65LVCP22PWR	ACTIVE	TSSOP	PW	16	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	LVCP22	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

**Green:** TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

# **PACKAGE OPTION ADDENDUM**



10-Dec-2020

**Important Information and Disclaimer:** The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

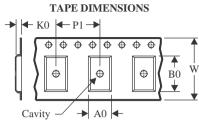
In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.



www.ti.com 5-Dec-2023

# TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

#### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



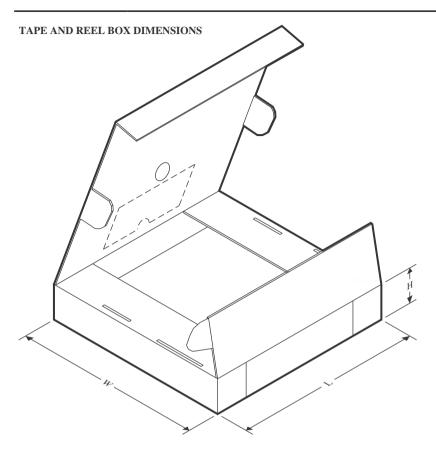
#### \*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN65LVCP22DR	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1
SN65LVCP22PWR	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1



# **PACKAGE MATERIALS INFORMATION**

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#### \*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN65LVCP22DR	SOIC	D	16	2500	350.0	350.0	43.0
SN65LVCP22PWR	TSSOP	PW	16	2000	350.0	350.0	43.0





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# **TUBE**



#### \*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
SN65LVCP22D	D	SOIC	16	40	505.46	6.76	3810	4
SN65LVCP22DG4	D	SOIC	16	40	505.46	6.76	3810	4
SN65LVCP22PW	PW	TSSOP	16	90	530	10.2	3600	3.5

# D (R-PDS0-G16)

# PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AC.





SMALL OUTLINE PACKAGE



#### NOTES:

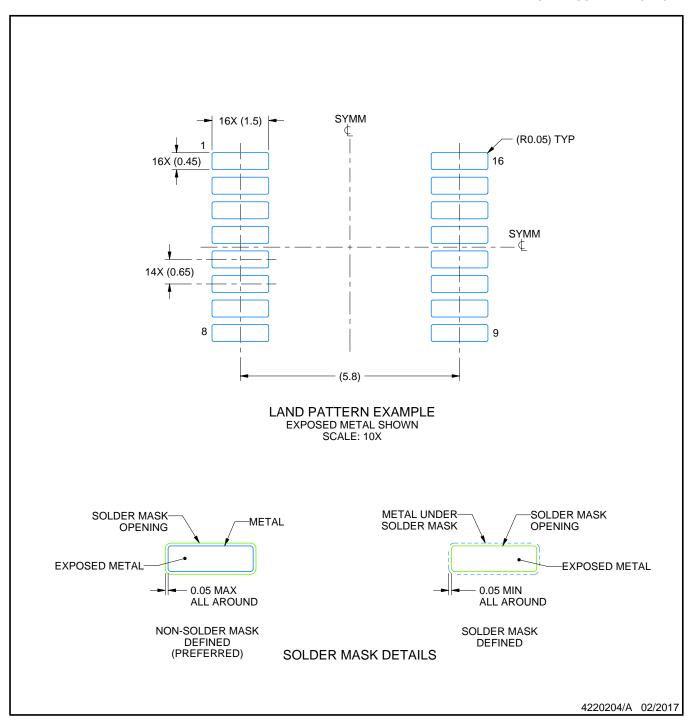
- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

  2. This drawing is subject to change without notice.

  3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153.



SMALL OUTLINE PACKAGE

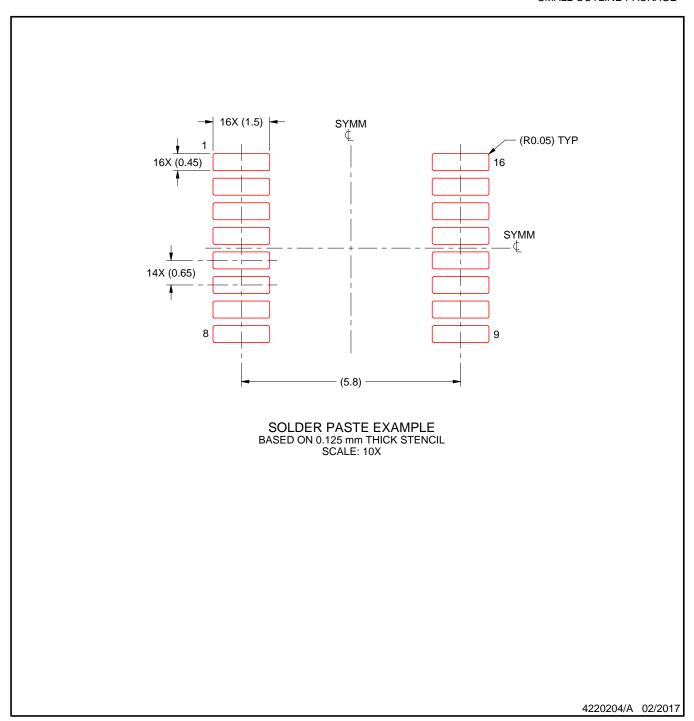


NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

SMALL OUTLINE PACKAGE



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



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